



## N-Channel 60-V (D-S) MOSFET

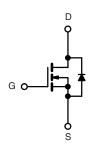
PRODUCT SUMMARY				
V <sub>DS</sub> (V)	$R_{DS(on)}(\Omega)$	I <sub>D</sub> (A)	Q <sub>g</sub> (Typ.)	
60	0.006 at V <sub>GS</sub> = 10 V	90 <sup>d</sup>	78.5	

#### **FEATURES**

- TrenchFET® Power MOSFET
- 175 °C Junction Temperature
- 100 %  $R_g$  and UIS Tested
- Compliant to RoHS Directive 2002/95/EC

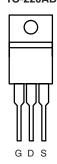
#### **APPLICATIONS**

- Power Supply
  - Secondary Synchronous Rectification
- Industrial



N-Channel MOSFET

#### **TO-220AB**



Top View

Ordering Information: SUP90N06-6m0P-E3 (Lead (Pb)-free)

<b>ABSOLUTE MAXIMUM RATINGS</b>	T <sub>C</sub> = 25 °C, unless oth	erwise noted		•
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V <sub>DS</sub>	60	V	
Gate-Source Voltage	V <sub>GS</sub>	± 20	7 °	
Continuous Drain Current (T <sub>.1</sub> = 175 °C)	T <sub>C</sub> = 25 °C	I-	90 <sup>d</sup>	
Continuous Diam Current (1) = 175 C)	T <sub>C</sub> = 70 °C	I <sub>D</sub>	90 <sup>d</sup>	<b>1</b>
Pulsed Drain Current	I <sub>DM</sub>	240	A	
Avalanche Current	I <sub>AS</sub>	50		
Single Avalanche Energy <sup>a</sup>	L = 0.1 mH	E <sub>AS</sub>	125	mJ
Mariana Barra Biraira iland	T <sub>C</sub> = 25 °C	В	272 <sup>b</sup>	10/
Maximum Power Dissipation <sup>a</sup>	T <sub>A</sub> = 25 °C <sup>c</sup>	P <sub>D</sub>	3.75	W
Operating Junction and Storage Temperature Range		T <sub>J</sub> , T <sub>stg</sub>	- 55 to 175	°C

THERMAL RESISTANCE RATINGS					
Parameter	Symbol	Limit	Unit		
Junction-to-Ambient (PCB Mount) <sup>c</sup>	R <sub>thJA</sub>	40	°C/W		
Junction-to-Case (Drain)	R <sub>thJC</sub>	0.55	C/VV		

#### Notes:

- a. Duty cycle  $\leq$  1 %.
- b. See SOA curve for voltage derating.c. When Mounted on 1" square PCB (FR-4 material).
- d. Package limited.

## SUP90N06-6m0P

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit	
Static							
Drain-Source Breakdown Voltage	$V_{DS}$	$V_{DS} = 0 \text{ V}, I_{D} = 250 \mu\text{A}$	60		V		
Gate Threshold Voltage	V <sub>GS(th)</sub>	$V_{DS} = V_{GS}, I_D = 250 \mu A$	2.5		4.5	7 V	
Gate-Body Leakage	I <sub>GSS</sub>	$V_{DS} = 0 \text{ V}, V_{GS} = \pm 20 \text{ V}$			± 250	nA	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V			1		
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 125 °C			50	μΑ	
		V <sub>DS</sub> = 60 V, V <sub>GS</sub> = 0 V, T <sub>J</sub> = 150 °C	C 250		250		
On-State Drain Current <sup>a</sup>	I <sub>D(on)</sub>	$V_{DS} \ge 10 \text{ V}, V_{GS} = 10 \text{ V}$	70			Α	
D : 0	D	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A		0.005	0.006		
Drain-Source On-State Resistance <sup>a</sup>	R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 20 A, T <sub>J</sub> = 125 °C		0.008	0.010	Ω	
Forward Transconductance <sup>a</sup>	9 <sub>fs</sub>	V <sub>DS</sub> = 15 V, I <sub>D</sub> = 20 A		58		S	
Dynamic <sup>b</sup>	•						
Input Capacitance	C <sub>iss</sub>			4700			
Output Capacitance	C <sub>oss</sub>	$V_{GS} = 0 \text{ V}, V_{DS} = 30 \text{ V}, f = 1 \text{ MHz}$		620		pF	
Reverse Transfer Capacitance	C <sub>rss</sub>			250			
Total Gate Charge <sup>c</sup>	$Q_g$			78.5	120		
Gate-Source Charge <sup>c</sup>	$Q_{gs}$	$V_{DS} = 30 \text{ V}, V_{GS} = 10 \text{ V}, I_D = 50 \text{ A}$		28		nC	
Gate-Drain Charge <sup>c</sup>	$Q_{gd}$			20.6			
Gate Resistance	R <sub>g</sub>	f = 1 MHz		1.2	2.4	Ω	
Turn-On Delay Time <sup>c</sup>	t <sub>d(on)</sub>			16	30		
Rise Time <sup>c</sup>	t <sub>r</sub>	$V_{DD}$ = 30 V, $R_L$ = 0.6 $\Omega$		10	20		
Turn-Off Delay Time <sup>c</sup>	t <sub>d(off)</sub>	$I_D \cong 50 \text{ A}, V_{GEN} = 10 \text{ V}, R_g = 1 \Omega$		25	40	ns	
Fall Time <sup>c</sup>	t <sub>f</sub>			8	15		
Source-Drain Diode Ratings and Cha	aracteristics	T <sub>C</sub> = 25 °C <sup>b</sup>					
Continuous Current	I <sub>S</sub>				85	_	
Pulsed Current	I <sub>SM</sub>				240	Α	
Forward Voltage <sup>a</sup>	V <sub>SD</sub>	I <sub>F</sub> = 20 A, V <sub>GS</sub> = 0 V		0.83	1.5	V	
Reverse Recovery Time	t <sub>rr</sub>			62	100	ns	
Peak Reverse Recovery Current	I <sub>RM(REC)</sub>	I <sub>F</sub> = 75 A, dl/dt = 100 A/μs		3.8	5.7	Α	
Reverse Recovery Charge	Q <sub>rr</sub>			118	180	nC	

#### Notes:

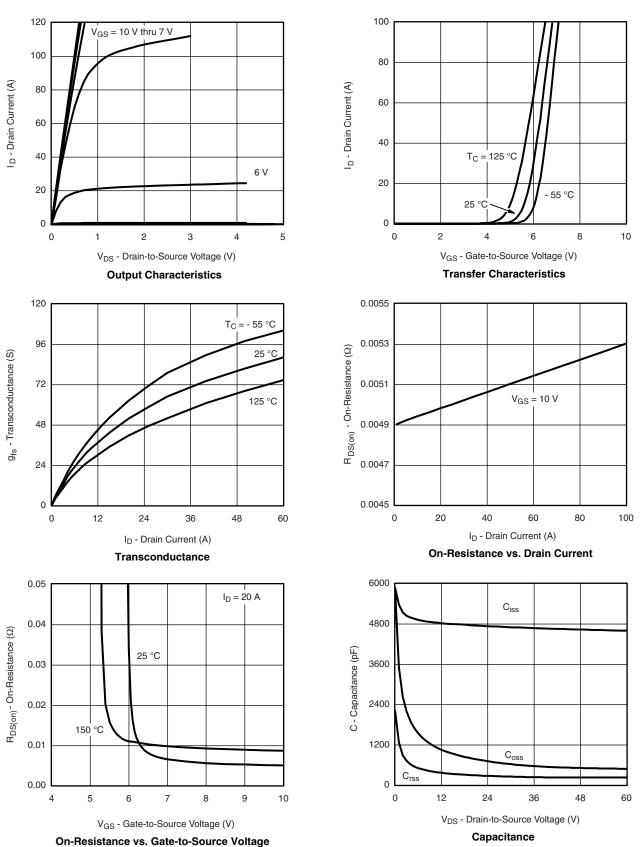
- a. Pulse test; pulse width  $\leq 300~\mu s,$  duty cycle  $\leq 2~\%.$
- b. Guaranteed by design, not subject to production testing.
- c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.





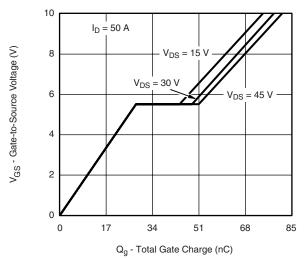
## TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted



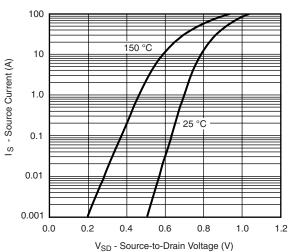
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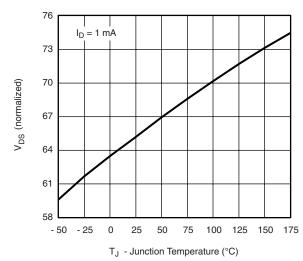
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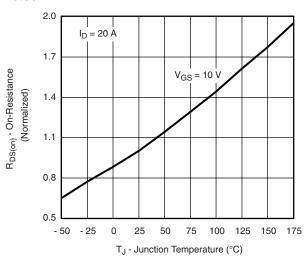
#### On-Resistance vs. Junction Temperature



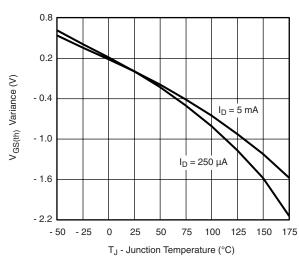
Gate Charge



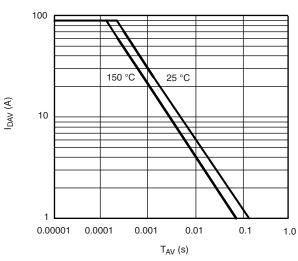
Source-Drain Diode Forward Voltage



Threshold Voltage



On-Resistance vs. Junction Temperature

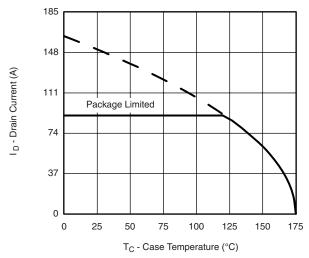


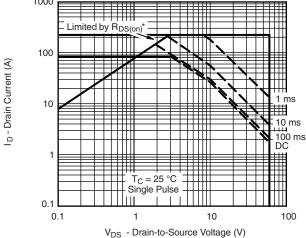
**Maximum Drain Current vs. Case Temperature** 



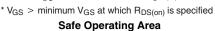
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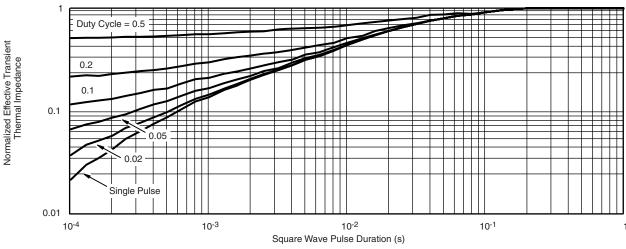
### TYPICAL CHARACTERISTICS 25 °C, unless otherwise noted





Single Pulse Avalanche Current Capability vs. Time





Normalized Thermal Transient Impedance, Junction-to-Case

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## **TO-220AB**



	D2

	MILLIMETERS		INCHES	
DIM.	MIN.	MAX.	MIN.	MAX.
А	4.25	4.65	0.167	0.183
b	0.69	1.01	0.027	0.040
b(1)	1.20	1.73	0.047	0.068
С	0.36	0.61	0.014	0.024
D	14.85	15.49	0.585	0.610
D2	12.19	12.70	0.480	0.500
Е	10.04	10.51	0.395	0.414
е	2.41	2.67	0.095	0.105
e(1)	4.88	5.28	0.192	0.208
F	1.14	1.40	0.045	0.055
H(1)	6.09	6.48	0.240	0.255
J(1)	2.41	2.92	0.095	0.115
L	13.35	14.02	0.526	0.552
L(1)	3.32	3.82	0.131	0.150
ØΡ	3.54	3.94	0.139	0.155
Q	2.60	3.00	0.102	0.118
ECN: T14-0413-Rev. P, 16-Jun-14 DWG: 5471				

#### Note

 $<sup>^{\</sup>star}$  M = 1.32 mm to 1.62 mm (dimension including protrusion) Heatsink hole for HVM



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